

ABSTRACT OF THE DISCLOSURE

A photoresist polymer remover composition for removing photoresist residuals generated from etching or ashing sub-processes. The disclosed photoresist polymer remover composition includes: (a) 5% to 15% of sulfuric acid based on the total weight of said composition, (b) 1% to 5% of hydrogen peroxide or 0.0001% to 0.05% of ozone based on the total weight of said composition, (c) 0.1% to 5% of acetic acid based on the total weight of said composition, (d) 0.0001% to 0.5% of ammonium fluoride based on the total weight of said composition and (e) remaining amount of water.